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Attorney Docket No. P119-US

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of: Doan et al.

Art Unit: 1765

Serial No.: 10/805,610

Examiner: Not Yet Assigned

Filed: 3/18/04

For: **A MICROELECTROMECHANICAL STRUCTURE AND A  
METHOD FOR MAKING THE SAME**

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 CFR 1.97(b)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-145

Sir:

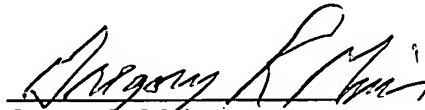
The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO Form 1449. Copies of the cited references are enclosed.

No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the last of (1) issuance of a first official action on the merits and (2) expiration of the three month period following filing of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can determine any materiality thereof to the claimed invention. It is respectfully requested that the information be considered during the prosecution of this application and that the cited documents be listed on the front page of any patent issuing from this application.

The Patent Office is authorized to charge our Deposit Account No. 501516 for any fee which it deems to be required to effect consideration of this statement.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Gregory R. Muir", is written over a horizontal line.

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PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

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			<b>Application Number</b>	10/805,610	
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			<b>First Named Inventor</b>	Doan	
			<b>Art Unit</b>	1765	
<b>Examiner Name</b>	Not Yet Assigned				
<b>Sheet</b>	1	of	6	<b>Attorney Docket Number</b>	P119-US

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
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		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
		EP-0704884-A2 ✓	04-03-1996	Mehta, J.		
		EP-0822582-A2 ✓	02-04-1998	Bhardwai, J.K.		
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		WO-98/32163 ✓	07-23-1998	Tai et al.		

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		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
		US- 6,396,619 B1	05-28-2002	Huibers, et al.	
		US- 6,576,489 B2	06/10/03	Leung, et a	
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		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
		JP-1997/09251981-A ✓	09-22-1997	Kazuaki et al.		
		JP-1998/10313128-A ✓	11-24-1998	Hanmin et al.		
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		JP-1986/61187238-A ✓	08-20-1986	Nobuo et al.		
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		JP-1986/61181131-A ✓	08-13-1986	Shinji et al.		

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				Art Unit	1765
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		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
		JP-1989/01208834-A	08-22-1989	Nobuo et al.		
		JP-1989/10217921-A	08-31-1989	Tsuneo et al.		
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		JP-1992/04096222-A	03-27-1992	Atsuyuki, A.		
		JP-1995/07029823-A	01-31-1995	Hiroshi, T.		

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		Filing Date	3/18/04
		First Named Inventor	Doan
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		Examiner Name	Not Yet Assigned
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Sheet	4	of	6

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		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F2 and XeF2 Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
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		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
		WINTERS et al., "The Etching of Silicon with XeF <sub>2</sub> Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
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		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF <sub>2</sub> Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
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		SEBEL et al., "Etching of Si Through a Thick Condensed XeF <sub>2</sub> Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

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